

Major Ratings and Characteristics

$I_{F(AV)}$	1.0 A
V_{RRM}	50 V to 1000 V
I_{FSM}	25 A
I_R	5 μ A
V_F	1.1 V
$T_j \text{ max.}$	150 °C

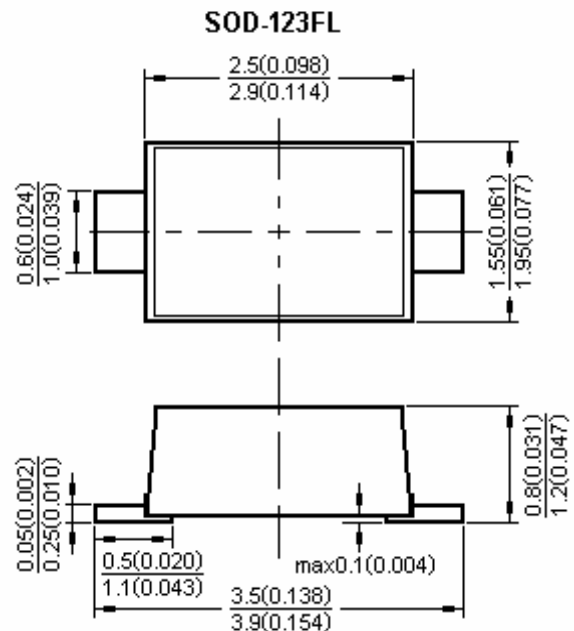


Features

- Low profile space
- Ideal for automated placement
- Glass passivated chip junctions
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High temperature soldering:
260°C/10 seconds at terminals
- Component in accordance to
RoHS 2002/95/1 and WEEE 2002/96/EC

Mechanical Data

- **Case:** JEDEC SOD-123FL molded plastic body over glass passivated chip
- **Terminals:** Solder plated, solderable per J-STD-002B and JESD22-B102D
- **Polarity:** Laser band denotes cathode end



Dimensions in millimeters and (inches)

Maximum Ratings & Thermal Characteristics & Electrical Characteristics

($T_A = 25\text{ °C}$ unless otherwise noted)

	Symbol	DSR1A	DSR1B	DSR1D	DSR1G	DSR1J	DSR1K	DSR1M	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	1							A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	25							A
Maximum instantaneous forward voltage at 1.0A	V_F	1.1							V
Maximum DC reverse current $T_A = 25\text{ °C}$ at Rated DC blocking voltage $T_A = 125\text{ °C}$	I_R	5.0 50							μ A
Typical junction capacitance at 4.0 V ,1MHz	C_J	15							p F
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							°C

Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward Current Derating Curve

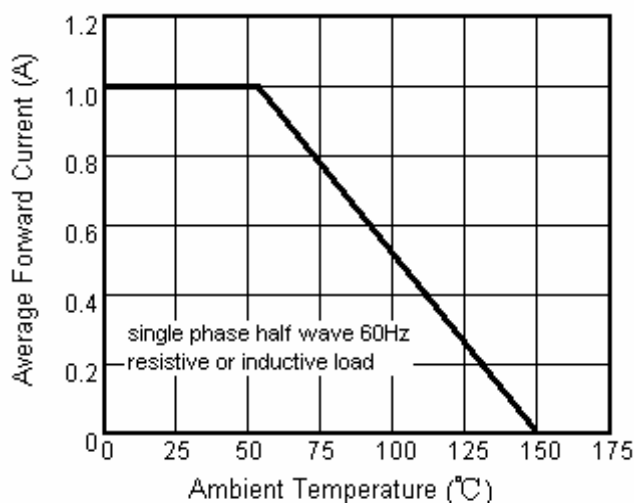


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

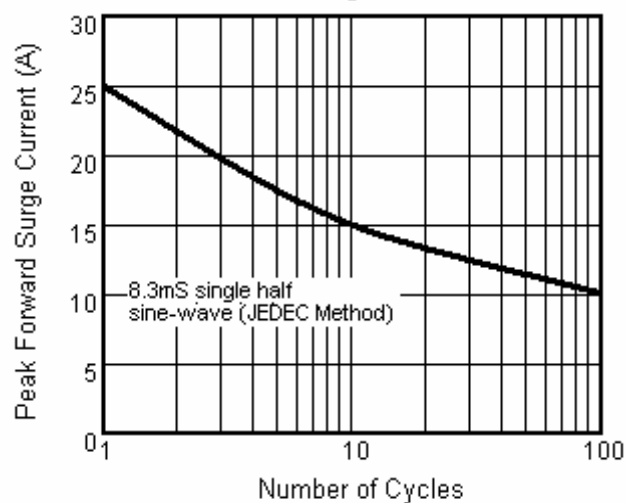


Fig.3 Typical Instantaneous Forward Characteristics

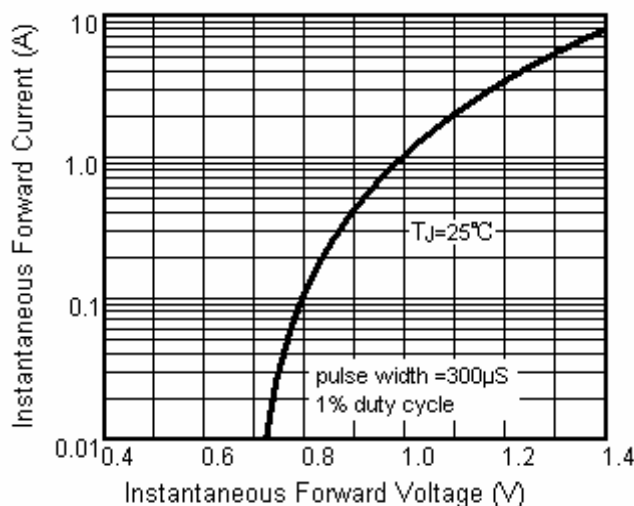


Fig.4 Typical Reverse Characteristics

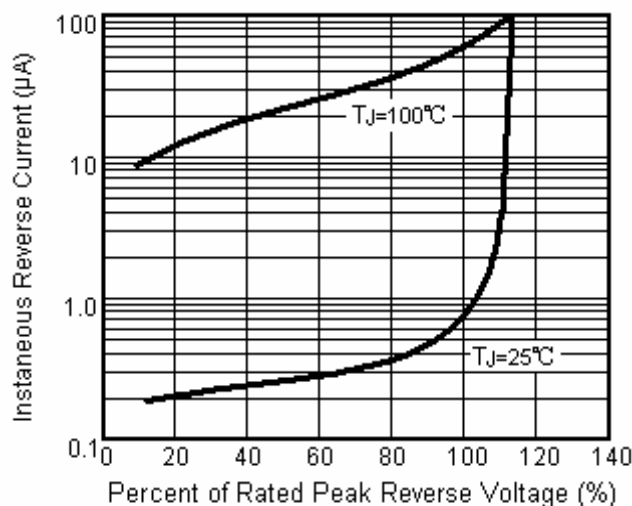


Fig.5 Typical Junction Capacitance

